

**14A, 50V, 0.100 Ohm, Logic Level,
N-Channel Power MOSFETs**

These are N-channel power MOSFETs manufactured using the MegaFET process. This process, which uses feature sizes approaching those of LSI integrated circuits, gives optimum utilization of silicon, resulting in outstanding performance. They were designed for use in applications such as switching regulators, switching converters, motor drivers and relay drivers. This performance is accomplished through a special gate oxide design which provides full rated conductance at gate bias in the 3V-5V range, thereby facilitating true on-off power control directly from logic level (5V) integrated circuits.

Formerly developmental type TA09870.

Ordering Information

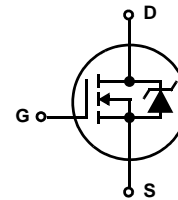
PART NUMBER	PACKAGE	BRAND
RFD14N05L	TO-251AA	14N05L
RFD14N05LSM	TO-252AA	14N05L

NOTE: When ordering, use the entire part number. Add the suffix 9A to obtain the TO-252AA variant in the tape and reel, i.e., RFD14N05LSM9A.

Features

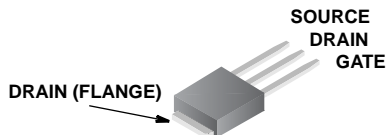
- 14A, 50V
- $r_{DS(ON)} = 0.100\Omega$
- Temperature Compensating PSpice® Model
- Can be Driven Directly from CMOS, NMOS, and TTL Circuits
- Peak Current vs Pulse Width Curve
- UIS Rating Curve
- 175°C Operating Temperature
- Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol

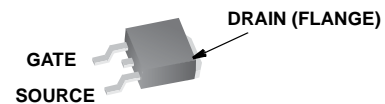


Packaging

JEDEC TO-251AA



JEDEC TO-252AA



RFD14N05L, RFD14N05LSM

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

	RFD14N05L, RFD14N05LSM,	UNITS
Drain to Source Voltage (Note 1).....	V_{DSS} 50	V
Drain to Gate Voltage ($R_{GS} = 20k\Omega$) (Note 1)	V_{DGR} 50	V
Gate to Source Voltage	V_{GS} ± 10	V
Continuous Drain Current	I_D 14	A
Pulsed Drain Current (Note 3)	I_{DM} Refer to Peak Current Curve	
Pulsed Avalanche Rating	E_{AS} Refer to UIS Curve	
Power Dissipation	P_D 48	W
Derate above 25°C	0.32	W/ $^\circ\text{C}$
Operating and Storage Temperature	T_J, T_{STG} -55 to 175	$^\circ\text{C}$
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s.....	T_L 300	$^\circ\text{C}$
Package Body for 10s, See Techbrief 334	T_{pk} 260	$^\circ\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

- $T_J = 25^\circ\text{C}$ to 150°C .

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS	
Drain to Source Breakdown Voltage	BV_{DSS}	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$, Figure 13	50	-	-	V	
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$, Figure 12	1	-	2	V	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 40\text{V}, V_{GS} = 0\text{V}$	-	-	1	μA	
		$V_{DS} = 40\text{V}, V_{GS} = 0\text{V}, T_C = 150^\circ\text{C}$	-	-	50	μA	
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 10\text{V}$	-	-	± 100	nA	
Drain to Source On Resistance (Note 2)	$r_{DS(ON)}$	$I_D = 14\text{A}, V_{GS} = 5\text{V}$, Figures 9, 11	-	-	0.100	Ω	
Turn-On Time	$t_{(ON)}$	$V_{DD} = 25\text{V}, I_D = 7\text{A}, R_L = 3.57\Omega, V_{GS} = 5\text{V}, R_{GS} = 0.6\Omega$	-	-	60	ns	
Turn-On Delay Time	$t_{d(ON)}$		-	13	-	ns	
Rise Time	t_r		-	24	-	ns	
Turn-Off Delay Time	$t_{d(OFF)}$		-	42	-	ns	
Fall Time	t_f		-	16	-	ns	
Turn-Off Time	$t_{(OFF)}$		-	-	100	ns	
Total Gate Charge	$Q_{g(TOT)}$	$V_{GS} = 0\text{V}$ to 10V	$V_{DD} = 40\text{V}, I_D = 14\text{A}, R_L = 2.86\Omega$ Figures 20, 21	-	-	40	nC
Gate Charge at 5V	$Q_{g(5)}$	$V_{GS} = 0\text{V}$ to 5V		-	-	25	nC
Threshold Gate Charge	$Q_{g(TH)}$	$V_{GS} = 0\text{V}$ to 1V		-	-	1.5	nC
Input Capacitance	C_{ISS}	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$ Figure 14	-	670	-	pF	
Output Capacitance	C_{OSS}		-	185	-	pF	
Reverse Transfer Capacitance	C_{RSS}		-	50	-	pF	
Thermal Resistance Junction to Case	$R_{\theta JC}$		-	-	3.125	$^\circ\text{C/W}$	
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	TO-251 and TO-252	-	-	100	$^\circ\text{C/W}$	

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage (Note 2)	V_{SD}	$I_{SD} = 14\text{A}$	-	-	1.5	V
Diode Reverse Recovery Time	t_{rr}	$I_{SD} = 14\text{A}, dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	125	ns

NOTES:

- Pulse Test: Pulse Width $\leq 300\text{ms}$, Duty Cycle $\leq 2\%$.
- Repetitive Rating: Pulse Width limited by max junction temperature. See Transient Thermal Impedance Curve (Figure 3) and Peak Current Capability Curve (Figure 5).

Typical Performance Curves Unless Otherwise Specified

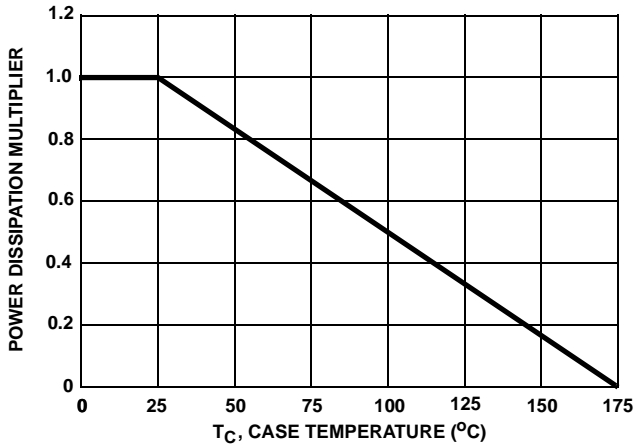


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

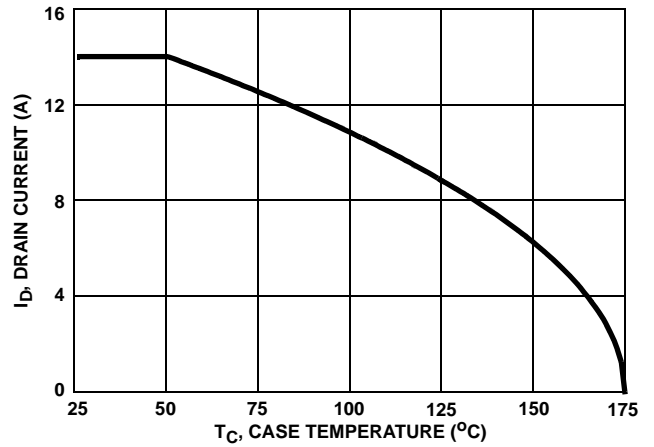


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs TEMPERATURE

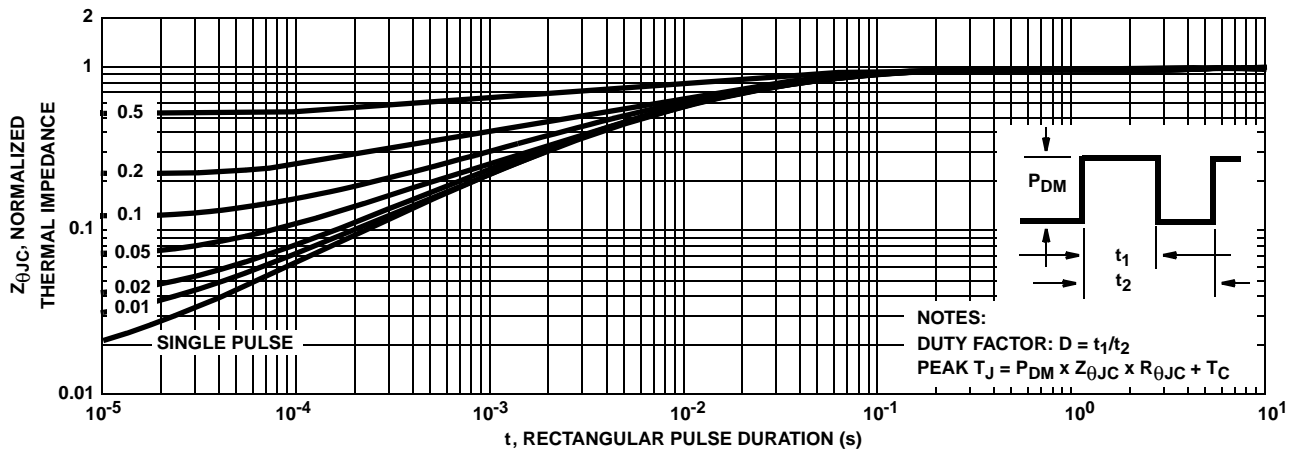


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

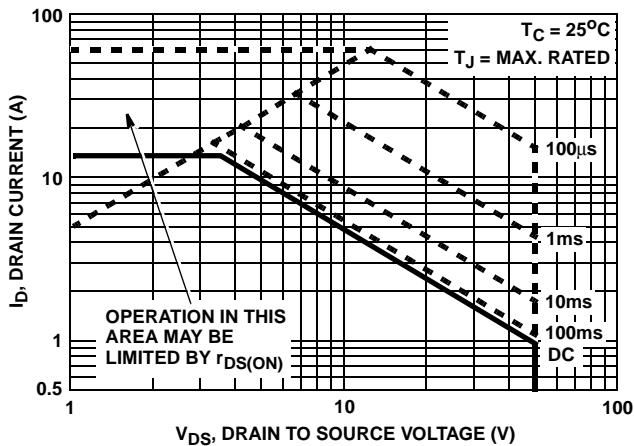


FIGURE 4. FORWARD BIAS SAFE OPERATING AREA

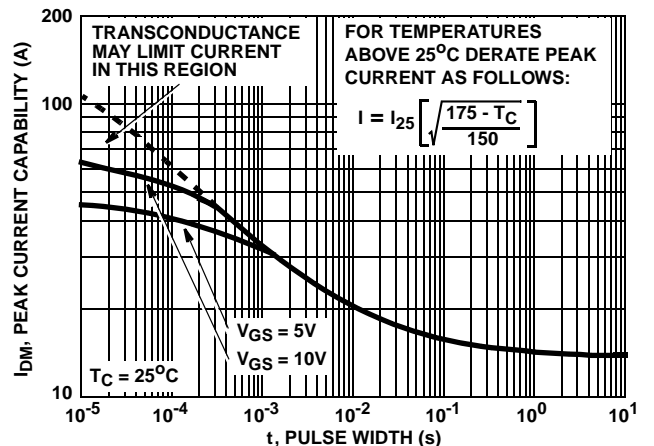
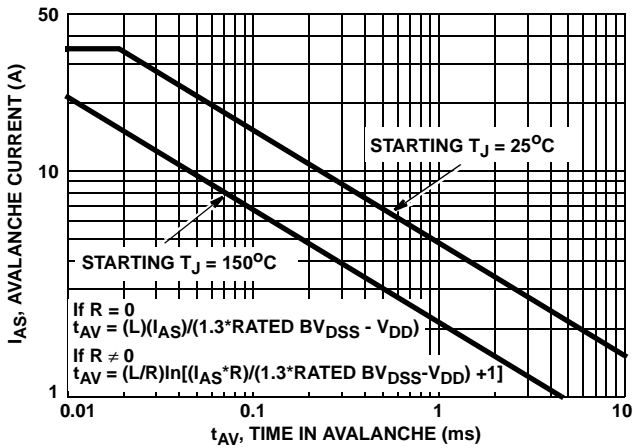


FIGURE 5. PEAK CURRENT CAPABILITY

Typical Performance Curves Unless Otherwise Specified (Continued)



NOTE: Refer to Fairchild Application Notes AN9321 and AN9322.

FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING

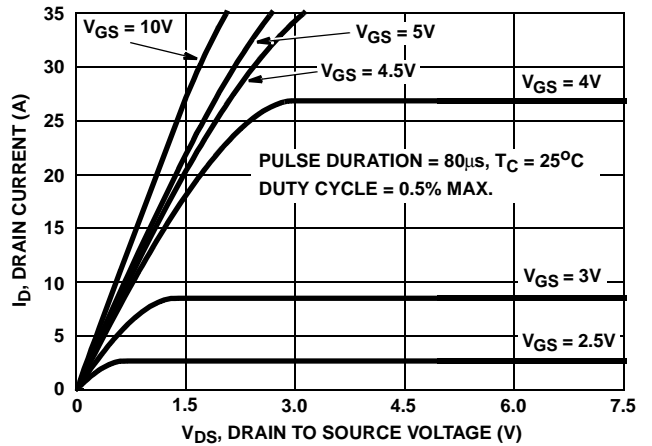


FIGURE 7. SATURATION CHARACTERISTICS

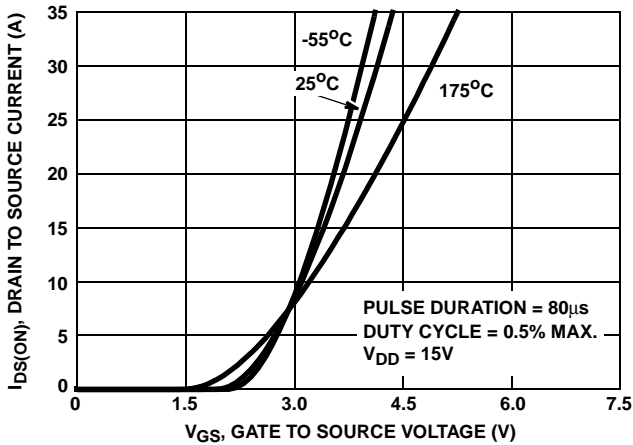


FIGURE 8. TRANSFER CHARACTERISTICS

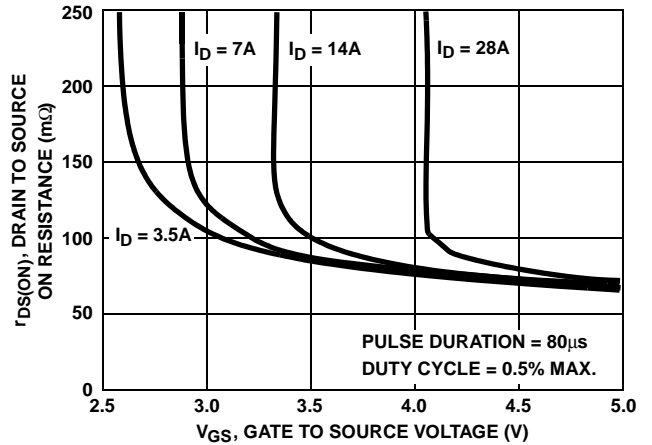


FIGURE 9. DRAIN TO SOURCE ON RESISTANCE vs GATE VOLTAGE AND DRAIN CURRENT

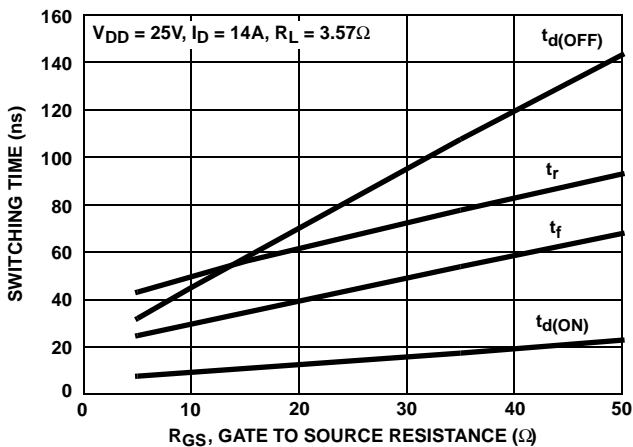


FIGURE 10. SWITCHING TIME vs GATE RESISTANCE

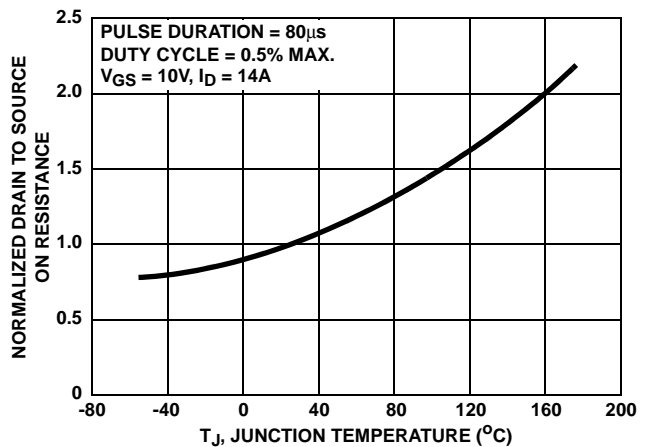


FIGURE 11. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

Typical Performance Curves Unless Otherwise Specified (Continued)

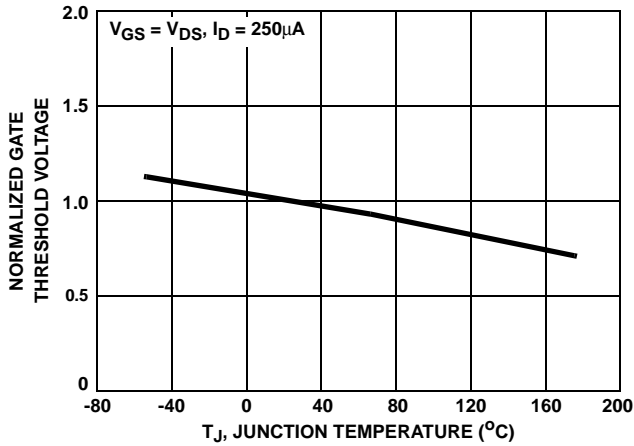


FIGURE 12. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

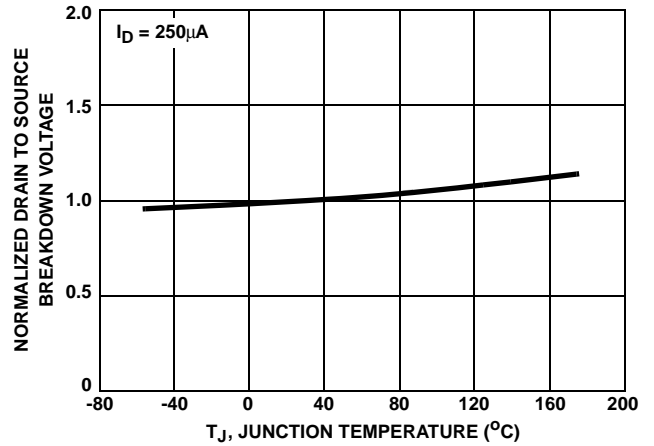


FIGURE 13. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

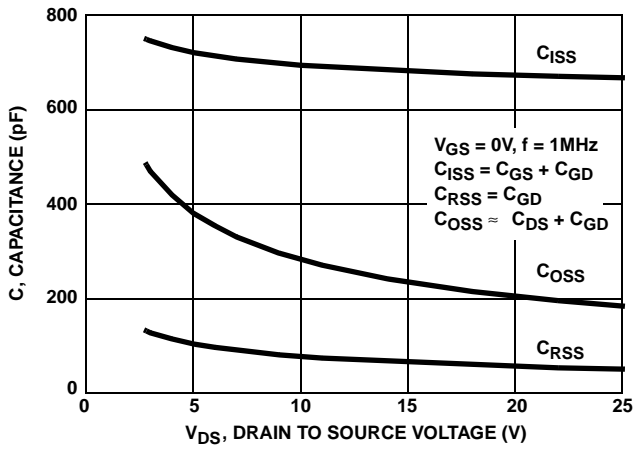
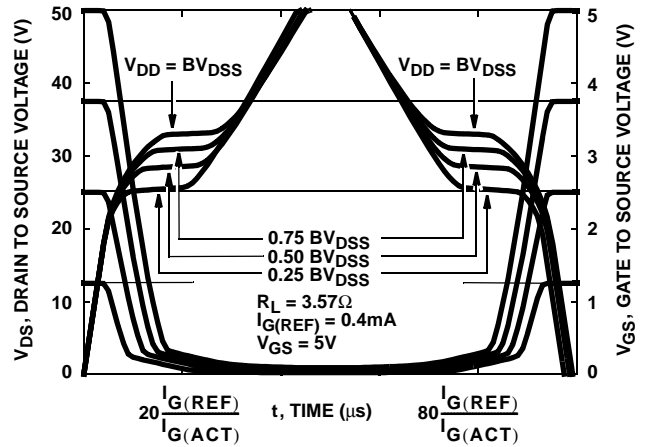


FIGURE 14. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE



NOTE: Refer to Fairchild Application Notes AN7254 and AN7260, FIGURE 15. TRANSCONDUCTANCE vs DRAIN CURRENT

Test Circuits and Waveforms

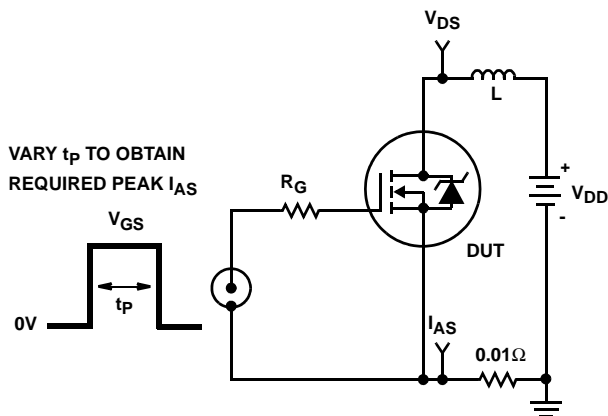


FIGURE 16. UNCLAMPED ENERGY TEST CIRCUIT

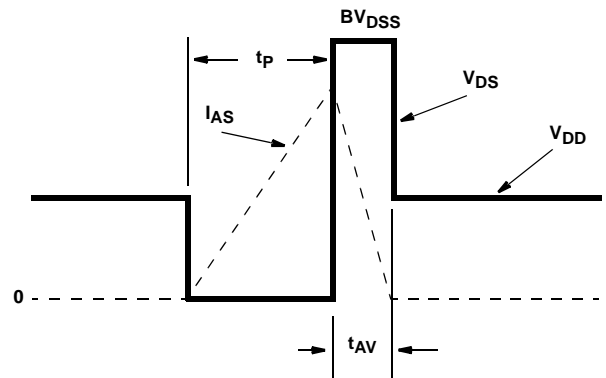


FIGURE 17. UNCLAMPED ENERGY WAVEFORMS

Test Circuits and Waveforms (Continued)

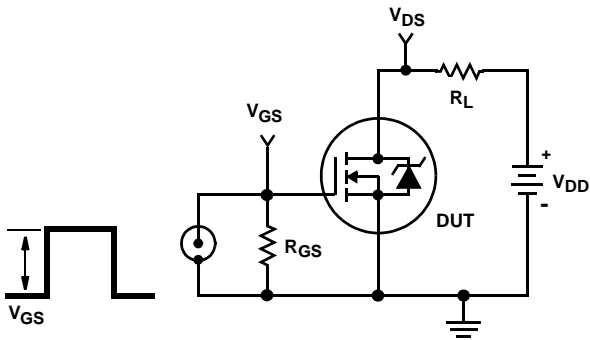


FIGURE 18. SWITCHING TIME TEST CIRCUIT

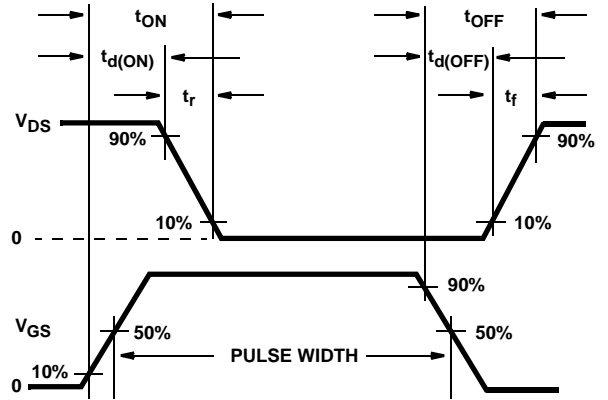


FIGURE 19. RESISTIVE SWITCHING WAVEFORMS

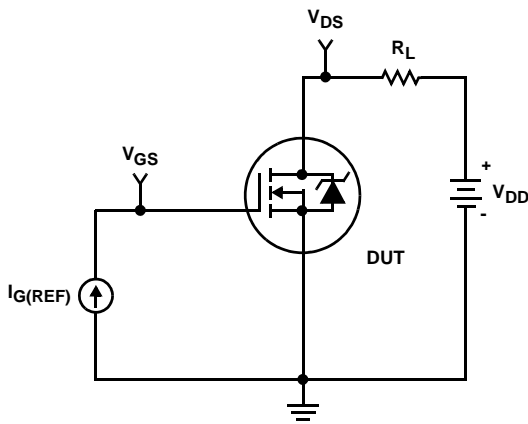


FIGURE 20. GATE CHARGE TEST CIRCUIT

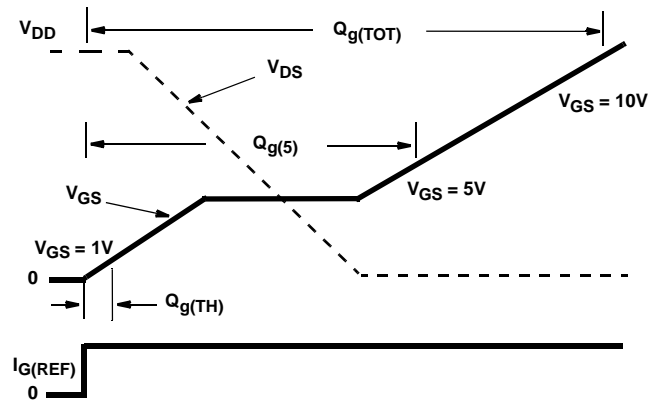


FIGURE 21. GATE CHARGE WAVEFORMS

RFD14N05L, RFD14N05LSM

PSPICE Electrical Model

.SUBCKT RFD14N05L 2 1 3 ; rev 9/15/94

CA 12 8 1.464e-9
 CB 15 14 1.64e-9
 CIN 6 8 6.17e-10

DBODY 7 5 DBDMOD
 DBREAK 5 11 DBKMOD
 DPLCAP 10 5 DPLCAPMOD

EBREAK 11 7 17 18 65.35
 EDS 14 8 5 8 1
 EGS 13 8 6 8 1
 ESG 6 10 6 8 1
 EVTO 20 6 18 8 1

IT 8 17 1

LDRAIN 2 5 1e-9
 LGATE 1 9 5.68e-9
 LSOURCE 3 7 5.35e-9

MOS1 16 6 8 8 MOSMOD M = 0.99
 MOS2 16 21 8 8 MOSMOD M = 0.01

RBREAK 17 18 RBKMOD 1
 RDRAIN 50 16 RDSMOD 33.1e-3
 RGATE 9 20 5.85
 RIN 6 8 1e9
 RSCL1 5 51 RSCLMOD 1e-6
 RSCL2 5 50 1e3
 RSOURCE 8 7 RDSMOD 14.3e-3
 RVTO 18 19 RVTOMOD 1

S1A 6 12 13 8 S1AMOD
 S1B 13 12 13 8 S1BMOD
 S2A 6 15 14 13 S2AMOD
 S2B 13 15 14 13 S2BMOD

VBAT 8 19 DC 1
 VTO 21 6 0.485

ESCL 51 50 VALUE = {(V(5,51)/ABS(V(5,51)))*(PWR(V(5,51)*1e6/46,7))}

.MODEL DBDMOD D (IS = 2.23e-13 RS = 1.15e-2 TRS1 = 1.64e-3 TRS2 = 7.89e-6 CJO = 6.83e-10 TT = 3.68e-8)

.MODEL DBKMOD D (RS = 3.8e-1 TRS1 = 1.89e-3 TRS2 = 1.13e-5)

.MODEL DPLCAPMOD D (CJO = 25.7e-11 IS = 1e-30 N = 10)

.MODEL MOSMOD NMOS (VTO = 1.935 KP = 18.89 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u)

.MODEL RBKMOD RES (TC1 = 7.18e-4 TC2 = 1.53e-6)

.MODEL RDSMOD RES (TC1 = 4.45e-3 TC2 = 2.9e-5)

.MODEL RSCLMOD RES (TC1 = 2.8e-3 TC2 = 6.0e-6)

.MODEL RVTOMOD RES (TC1 = -1.7e-3 TC2 = -2.0e-6)

.MODEL S1AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -3.55 VOFF = -1.55)

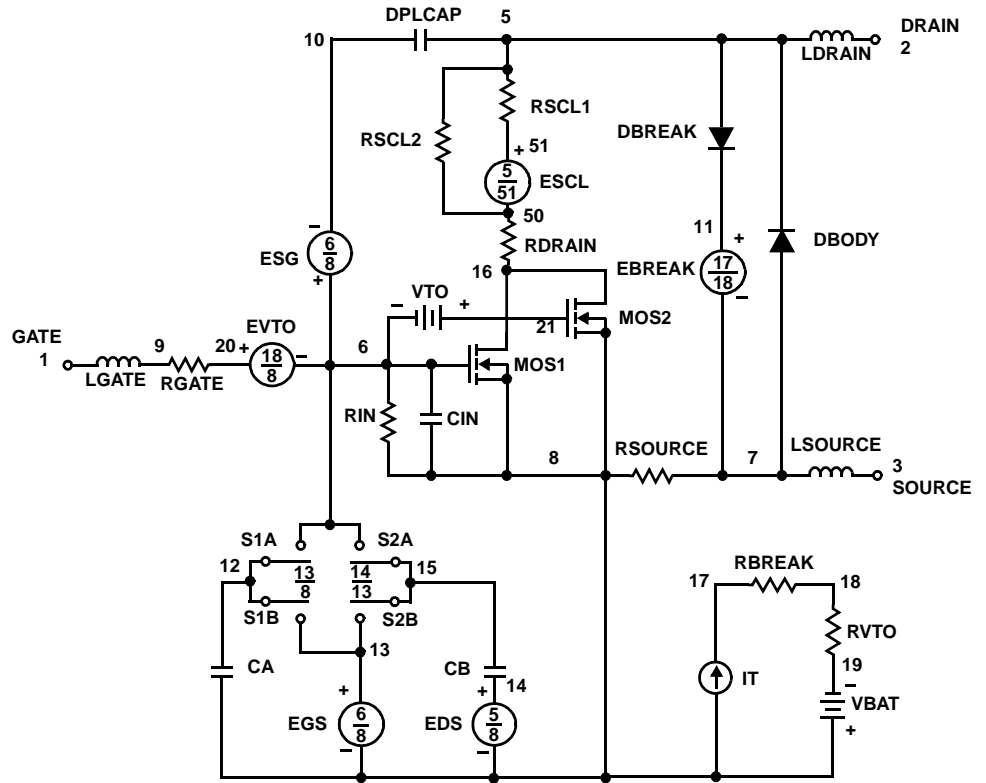
.MODEL S1BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -1.55 VOFF = -3.55)

.MODEL S2AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -2.55 VOFF = 2.45)

.MODEL S2BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = 2.45 VOFF = -2.55)

.ENDS

NOTE: For further discussion of the PSPICE model, consult **A New PSPICE Sub-circuit for the Power MOSFET Featuring Global Temperature Options**; authored by William J. Hepp and C. Frank Wheatley.





TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

- | | | | |
|--------------------------|-------------------------------------|---------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| AccuPower™ | F-PFST™ | Power-SPM™ | <p>SYSTEM GENERAL®
The Power Franchise®</p> <p>the power®
franchise</p> <p>TinyBoost™</p> <p>TinyBuck™</p> <p>TinyCalc™</p> <p>TinyLogic®</p> <p>TINYOPTO™</p> <p>TinyPower™</p> <p>TinyPWM™</p> <p>TinyWire™</p> <p>TriFault Detect™</p> <p>TRUECURRENT™*</p> <p>µSerDes™</p> <p>UHC®</p> <p>Ultra FRFET™</p> <p>UniFET™</p> <p>VCX™</p> <p>VisualMax™</p> <p>XS™</p> |
| Auto-SPM™ | FRFET® | PowerTrench® | |
| Build it Now™ | Global Power Resource SM | PowerXS™ | |
| CorePLUS™ | Green FPS™ | Programmable Active Droop™ | |
| CorePOWER™ | Green FPS™ e-Series™ | QFET® | |
| CROSSVOLT™ | Gmax™ | QS™ | |
| CTL™ | GTO™ | Quiet Series™ | |
| Current Transfer Logic™ | IntelliMAX™ | RapidConfigure™ | |
| DEUXPEED® | ISOPLANAR™ | ™ | |
| Dual Cool™ | MegaBuck™ | Saving our world, 1mW/W/kW at a time™ | |
| EcoSPARK® | MICROCOUPLER™ | SignalWise™ | |
| EfficientMax™ | MicroFET™ | SmartMax™ | |
| ESBC™ | MicroPak™ | SMART START™ | |
| ® | MicroPak2™ | SPM® | |
| Fairchild® | MillerDrive™ | STEALTH™ | |
| Fairchild Semiconductor® | MotionMax™ | SuperFET™ | |
| FACT Quiet Series™ | Motion-SPM™ | SuperSOT™-3 | |
| FACT® | OptiHIT™ | SuperSOT™-6 | |
| FAST® | OPTOLOGIC® | SuperSOT™-8 | |
| FAST® | OPTOPLANAR® | SupreMOS™ | |
| FastvCore™ | ® | SyncFET™ | |
| FETBench™ | PDP SPM™ | Sync-Lock™ | |
| FlashWriter®* | | | |
| FPS™ | | | |

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.